Elektronische Bauelemente

SSG4835P

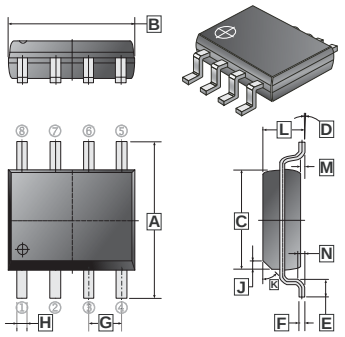
-9.5 A, -30 V, $R_{DS(ON)}$ 19 mΩ
P-Ch Enhancement Mode Power MOSFET

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

These miniature surface mount MOSFETs utilize high cell density process. Low $R_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

SOP-8



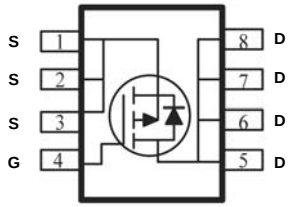
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	5.80	6.20	H	0.35	0.49
B	4.80	5.00	J	0.375 REF.	
C	3.80	4.00	K	45°	
D	0°	8°	L	1.35	1.75
E	0.40	0.90	M	0.10	0.25
F	0.19	0.25	N	0.25 REF.	
G	1.27 TYP.				

FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Miniature SOP-8 surface mount package saves board space.
- High power and current handling capability.
- Extended V_{GS} range (±25) for battery pack applications.

PACKAGE INFORMATION

Package	MPQ	LeaderSize
SOP-8	2.5K	13' inch



MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current [a]		I_D @ T_A = 25°C	-9.5	A
		I_D @ T_A = 70°C	-8.3	A
Pulsed Drain Current [b]		I_{DM}	±50	A
Continuous Source Current (Diode Conduction) [1]		I_S	-2.1	A
Total Power Dissipation [1]		P_D @ T_A = 25°C	3.1	W
		P_D @ T_A = 70°C	2.6	W
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 ~ 150	°C
Thermal Resistance Ratings				
Thermal Resistance Junction-Case (Max.) [1]	t ≦ 5 sec	$R_{\theta JC}$	25	°C / W
Thermal Resistance Junction-Ambient (Max.) [1]	t ≦ 10 sec	$R_{\theta JA}$	50	°C / W

Notes

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Teat Conditions
Static						
Gate Threshold Voltage	$V_{GS(th)}$	-1	-	-	V	V_{DS}= V_{GS}, I_D= -250μA
Gate-Body Leakage	I_{GSS}	-	-	±100	nA	V_{DS}= 0V, V_{GS}= ±25V
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	V_{DS}= -24V, V_{GS}= 0V
		-	-	-5	μA	V_{DS}= -24V, V_{GS}= 0V, T_J=55°C
On-State Drain Current [1]	$I_{D(on)}$	-50	-	-	A	V_{DS}= -5V, V_{GS}= -10V
Drain-Source On-Resistance [1]	$R_{DS(ON)}$	-	-	19	mΩ	V_{GS}= -10V, I_D= -9.5A
		-	-	30		V_{GS}= -4.5V, I_D= -7.5A
		-	-	29		V_{GS}= -10V, I_D= -9.5A, T_J=55°C
Forward Transconductance [1]	g_{fs}	-	31	-	S	V_{DS}= -15V, I_D= -9.5A
Diode Forward Voltage	V_{SD}	-	-0.7	-	V	I_S= -2.1A, V_{GS}= 0V
Dynamic [2]						
Total Gate Charge	Q_g	-	15.3	-	nC	I_D= -9.5A V_{DS}= -15V V_{GS}= -4.5V
Gate-Source Charge	Q_{gs}	-	5.2	-		
Gate-Drain Charge	Q_{gd}	-	5.8	-		
Switching						
Turn-On Delay Time	$T_{d(on)}$	-	15	-	nS	V_{DD}= -15V, I_D= -1A V_{GEN}= -10V, R_L= 15Ω R_G= 6Ω
Rise Time	T_r	-	12	-		
Turn-Off Delay Time	$T_{d(off)}$	-	62	-		
Fall Time	T_f	-	46	-		

Notes:

1. Pulse test : PW ≦ 300μs duty cycle ≦ 2%.
2. Guaranteed by design, not subject to production testing.

CHARACTERISTIC CURVES

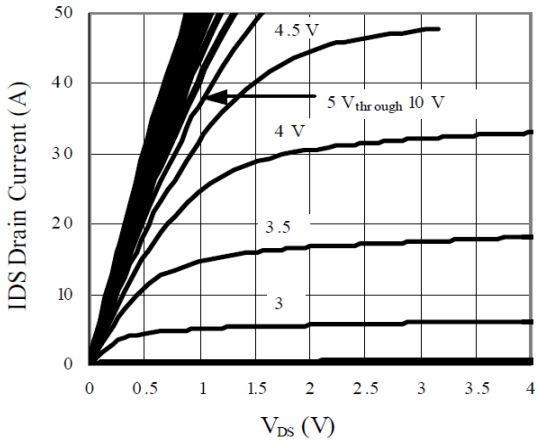


Figure 1. On-Region Characteristics

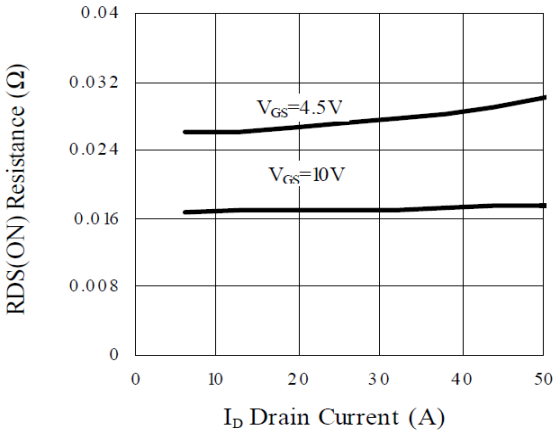


Figure 2. On-Resistance with Drain Current

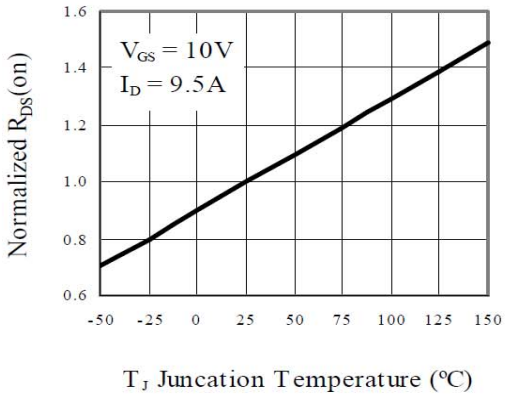


Figure 3. On-Resistance Variation with Temperature

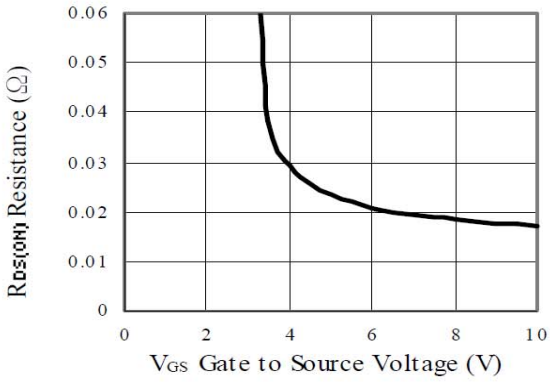


Figure 4. On-Resistance Variation with Gate to Source Voltage

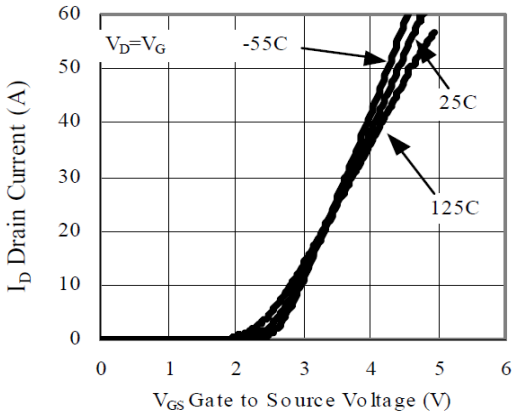


Figure 5. Transfer Characteristics

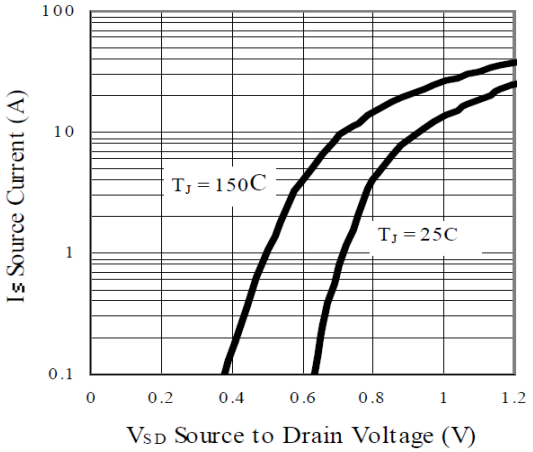


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

CHARACTERISTIC CURVES

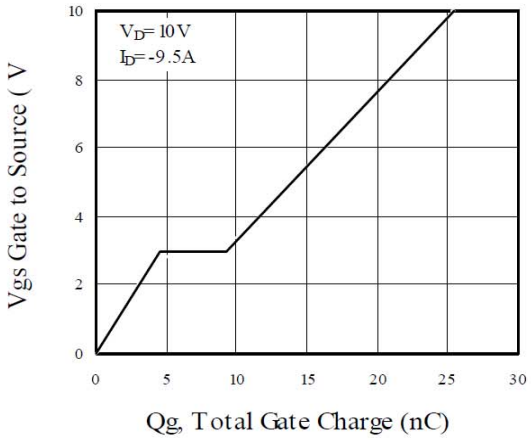


Figure 7. Gate Charge Characteristics

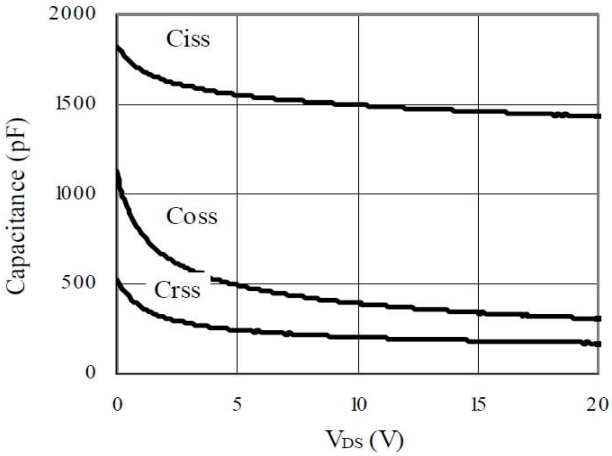


Figure 8. Capacitance Characteristics

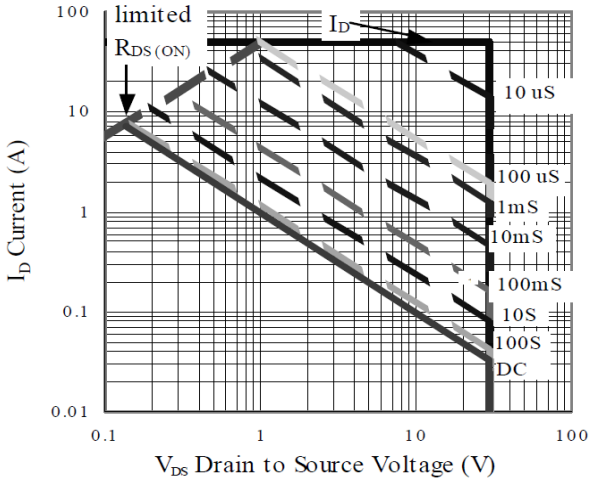


Figure 9. Maximum Safe Operating Area

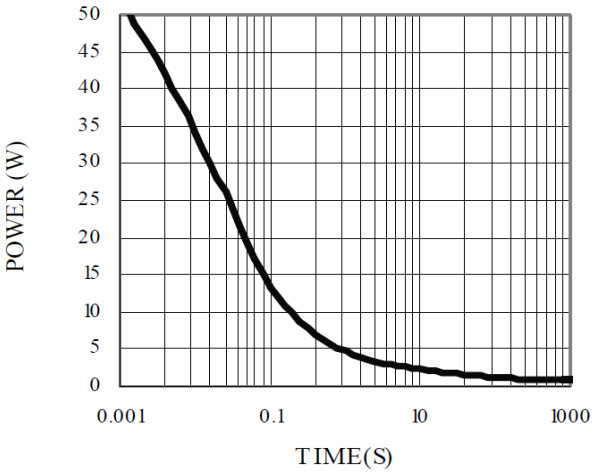


Figure 10. Single Pulse Maximum Power Dissipation

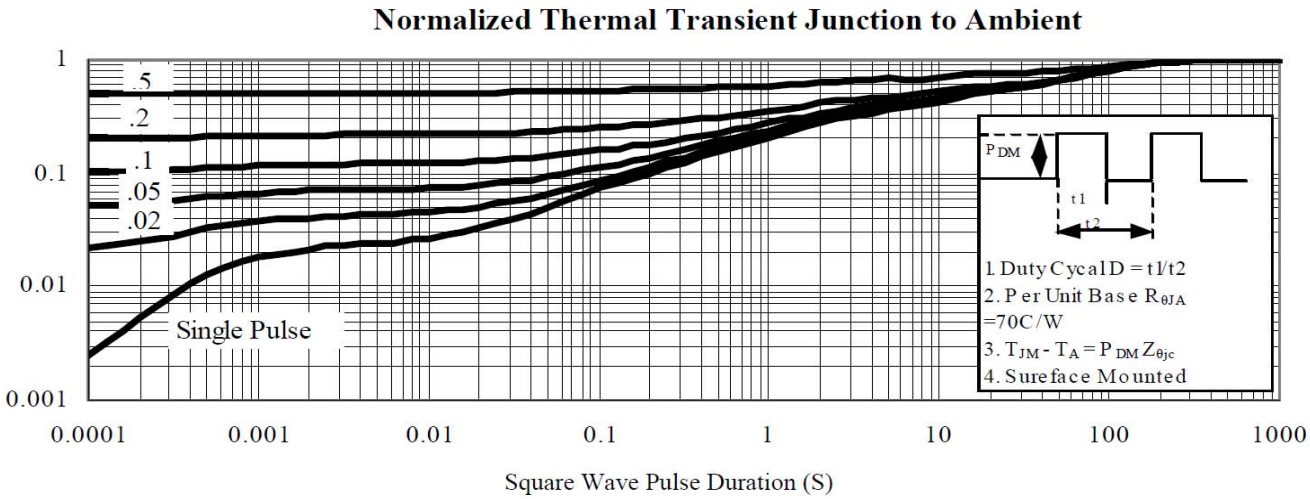


Figure 11. Transient Thermal Response Curve